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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications,

Details

Product Status	Active
Number of LABs/CLBs	2500
Number of Logic Elements/Cells	40000
Total RAM Bits	1290240
Number of I/O	101
Number of Gates	-
Voltage - Supply	2.85V ~ 3.465V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (Tj)
Package / Case	144-LQFP Exposed Pad
Supplier Device Package	144-EQFP (20x20)
Purchase URL	https://www.e-xfl.com/product-detail/intel/10m40sae144c8g



Symbol	Parameter	Condition	Min	Typ	Max	Unit
V _{CCA} ⁽¹⁾	Supply voltage for PLL regulator and ADC block (analog)	1.35 V	1.2825	1.35	1.4175	V
		1.2 V	1.14	1.2	1.26	V
V _{CCA} ⁽¹⁾	Supply voltage for PLL regulator and ADC block (analog)	—	2.85/3.135	3.0/3.3	3.15/3.465	V

Dual Supply Devices Power Supplies Recommended Operating Conditions

Table 7. Power Supplies Recommended Operating Conditions for Intel MAX 10 Dual Supply Devices

Symbol	Parameter	Condition	Min	Typ	Max	Unit
V _{CC}	Supply voltage for core and periphery	—	1.15	1.2	1.25	V
V _{CCIO} ⁽³⁾	Supply voltage for input and output buffers	3.3 V	3.135	3.3	3.465	V
		3.0 V	2.85	3	3.15	V
		2.5 V	2.375	2.5	2.625	V
		1.8 V	1.71	1.8	1.89	V
		1.5 V	1.425	1.5	1.575	V
		1.35 V	1.2825	1.35	1.4175	V
		1.2 V	1.14	1.2	1.26	V
V _{CCA} ⁽⁴⁾	Supply voltage for PLL regulator (analog)	—	2.375	2.5	2.625	V
V _{CCD_PLL} ⁽⁵⁾	Supply voltage for PLL regulator (digital)	—	1.15	1.2	1.25	V
V _{CCA_ADC}	Supply voltage for ADC analog block	—	2.375	2.5	2.625	V
V _{CCINT}	Supply voltage for ADC digital block	—	1.15	1.2	1.25	V

⁽³⁾ V_{CCIO} for all I/O banks must be powered up during user mode because V_{CCIO} I/O banks are used for the ADC and I/O functionalities.

⁽⁴⁾ All V_{CCA} pins must be powered to 2.5 V (even when PLLs are not used), and must be powered up and powered down at the same time.

⁽⁵⁾ V_{CCD_PLL} must always be connected to V_{CC} through a decoupling capacitor and ferrite bead.



Series OCT without Calibration Specifications

Table 13. Series OCT without Calibration Specifications for Intel MAX 10 Devices

This table shows the variation of on-chip termination (OCT) without calibration across process, voltage, and temperature (PVT).

Description	V _{CCIO} (V)	Resistance Tolerance		Unit
		-C7, -I6, -I7, -A6, -A7	-C8	
Series OCT without calibration	3.00	±35	±30	%
	2.50	±35	±30	%
	1.80	±40	±35	%
	1.50	±40	±40	%
	1.35	±40	±50	%
	1.20	±45	±60	%

Series OCT with Calibration at Device Power-Up Specifications

Table 14. Series OCT with Calibration at Device Power-Up Specifications for Intel MAX 10 Devices

OCT calibration is automatically performed at device power-up for OCT enabled I/Os.

Description	V _{CCIO} (V)	Calibration Accuracy	Unit
Series OCT with calibration at device power-up	3.00	±12	%
	2.50	±12	%
	1.80	±12	%
	1.50	±12	%
	1.35	±12	%
	1.20	±12	%

OCT Variation after Calibration at Device Power-Up

The OCT resistance may vary with the variation of temperature and voltage after calibration at device power-up.

Use the following table and equation to determine the final OCT resistance considering the variations after calibration at device power-up.



- Subscript x refers to both V and T.
- ΔR_V is variation of resistance with voltage.
- ΔR_T is variation of resistance with temperature.
- dR/dT is the change percentage of resistance with temperature after calibration at device power-up.
- dR/dV is the change percentage of resistance with voltage after calibration at device power-up.
- V_1 is the initial voltage.
- V_2 is final voltage.

The following figure shows the example to calculate the change of 50 Ω I/O impedance from 25°C at 3.0 V to 85°C at 3.15 V.

Figure 2. Example for OCT Resistance Calculation after Calibration at Device Power-Up

$$\Delta R_V = (3.15 - 3) \times 1000 \times -0.027 = -4.05$$

$$\Delta R_T = (85 - 25) \times 0.25 = 15$$

Because ΔR_V is negative,

$$MF_V = 1/(4.05/100 + 1) = 0.961$$

Because ΔR_T is positive,

$$MF_T = 15/100 + 1 = 1.15$$

$$MF = 0.961 \times 1.15 = 1.105$$

$$R_{final} = 50 \times 1.105 = 55.25\Omega$$



Pin Capacitance

Table 16. Pin Capacitance for Intel MAX 10 Devices

Symbol	Parameter	Maximum	Unit
C_{IOB}	Input capacitance on bottom I/O pins	8	pF
C_{IOLRT}	Input capacitance on left/right/top I/O pins	7	pF
C_{LVDSB}	Input capacitance on bottom I/O pins with dedicated LVDS output ⁽⁹⁾	8	pF
C_{ADCL}	Input capacitance on left I/O pins with ADC input ⁽¹⁰⁾	9	pF
$C_{VREFLRT}$	Input capacitance on left/right/top dual purpose V_{REF} pin when used as V_{REF} or user I/O pin ⁽¹¹⁾	48	pF
C_{VREFB}	Input capacitance on bottom dual purpose V_{REF} pin when used as V_{REF} or user I/O pin	50	pF
C_{CLKB}	Input capacitance on bottom dual purpose clock input pins ⁽¹²⁾	7	pF
C_{CLKLRT}	Input capacitance on left/right/top dual purpose clock input pins ⁽¹²⁾	6	pF

Internal Weak Pull-Up Resistor

All I/O pins, except configuration, test, and JTAG pins, have an option to enable weak pull-up.

⁽⁹⁾ Dedicated LVDS output buffer is only available at bottom I/O banks.

⁽¹⁰⁾ ADC pins are only available at left I/O banks.

⁽¹¹⁾ When V_{REF} pin is used as regular input or output, F_{max} performance is reduced due to higher pin capacitance. Using the V_{REF} pin capacitance specification from device datasheet, perform SI analysis on your board setup to determine the F_{max} of your system.

⁽¹²⁾ 10M40 and 10M50 devices have dual purpose clock input pins at top/bottom I/O banks.



Table 17. Internal Weak Pull-Up Resistor for Intel MAX 10 Devices

Pin pull-up resistance values may be lower if an external source drives the pin higher than V_{CCIO} .

Symbol	Parameter	Condition	Min	Typ	Max	Unit
R_{PU}	Value of I/O pin (dedicated and dual-purpose) pull-up resistor before and during configuration, as well as user mode if the programmable pull-up resistor option is enabled	$V_{CCIO} = 3.3 \text{ V} \pm 5\%$	7	12	34	$\text{k}\Omega$
		$V_{CCIO} = 3.0 \text{ V} \pm 5\%$	8	13	37	$\text{k}\Omega$
		$V_{CCIO} = 2.5 \text{ V} \pm 5\%$	10	15	46	$\text{k}\Omega$
		$V_{CCIO} = 1.8 \text{ V} \pm 5\%$	16	25	75	$\text{k}\Omega$
		$V_{CCIO} = 1.5 \text{ V} \pm 5\%$	20	36	106	$\text{k}\Omega$
		$V_{CCIO} = 1.2 \text{ V} \pm 5\%$	33	82	179	$\text{k}\Omega$

Hot-Socketing Specifications

Table 18. Hot-Socketing Specifications for Intel MAX 10 Devices

Symbol	Parameter	Maximum
$I_{IOPIN(DC)}$	DC current per I/O pin	300 μA
$I_{IOPIN(AC)}$	AC current per I/O pin	8 mA ⁽¹³⁾

Hysteresis Specifications for Schmitt Trigger Input

Intel MAX 10 devices support Schmitt trigger input on all I/O pins. A Schmitt trigger feature introduces hysteresis to the input signal for improved noise immunity, especially for signal with slow edge rate.

⁽¹³⁾ The I/O ramp rate is 10 ns or more. For ramp rates faster than 10 ns, $|I_{IOPIN}| = C \frac{dv}{dt}$, in which C is I/O pin capacitance and dv/dt is the slew rate.



Single-Ended SSTL, HSTL, and HSUL I/O Reference Voltage Specifications

Table 21. Single-Ended SSTL, HSTL, and HSUL I/O Reference Voltage Specifications for Intel MAX 10 Devices

I/O Standard	V _{CCIO} (V)			V _{REF} (V)			V _{TT} (V) (14)		
	Min	Typ	Max	Min	Typ	Max	Min	Typ	Max
SSTL-2 Class I, II	2.375	2.5	2.625	1.19	1.25	1.31	V _{REF} - 0.04	V _{REF}	V _{REF} + 0.04
SSTL-18 Class I, II	1.7	1.8	1.9	0.833	0.9	0.969	V _{REF} - 0.04	V _{REF}	V _{REF} + 0.04
SSTL-15 Class I, II	1.425	1.5	1.575	0.49 × V _{CCIO}	0.5 × V _{CCIO}	0.51 × V _{CCIO}	0.49 × V _{CCIO}	0.5 × V _{CCIO}	0.51 × V _{CCIO}
SSTL-135 Class I, II	1.283	1.35	1.45	0.49 × V _{CCIO}	0.5 × V _{CCIO}	0.51 × V _{CCIO}	0.49 × V _{CCIO}	0.5 × V _{CCIO}	0.51 × V _{CCIO}
HSTL-18 Class I, II	1.71	1.8	1.89	0.85	0.9	0.95	0.85	0.9	0.95
HSTL-15 Class I, II	1.425	1.5	1.575	0.71	0.75	0.79	0.71	0.75	0.79
HSTL-12 Class I, II	1.14	1.2	1.26	0.48 × V _{CCIO} ⁽¹⁵⁾	0.5 × V _{CCIO} ⁽¹⁵⁾	0.52 × V _{CCIO} ⁽¹⁵⁾	—	0.5 × V _{CCIO}	—
				0.47 × V _{CCIO} ⁽¹⁶⁾	0.5 × V _{CCIO} ⁽¹⁶⁾	0.53 × V _{CCIO} ⁽¹⁶⁾			
HSUL-12	1.14	1.2	1.3	0.49 × V _{CCIO}	0.5 × V _{CCIO}	0.51 × V _{CCIO}	—	—	—

(14) V_{TT} of transmitting device must track V_{REF} of the receiving device.

(15) Value shown refers to DC input reference voltage, V_{REF(DC)}.

(16) Value shown refers to AC input reference voltage, V_{REF(AC)}.



I/O Standard	V _{IL(DC)} (V)		V _{IH(DC)} (V)		V _{IL(AC)} (V)		V _{IH(AC)} (V)		V _{OL} (V)	V _{OH} (V)	I _{OL} (mA)	I _{OH} (mA)
	Min	Max	Min	Max	Min	Max	Min	Max	Max	Min		
HSTL-12 Class I	-0.15	V _{REF} - 0.08	V _{REF} + 0.08	V _{CCIO} + 0.15	-0.24	V _{REF} - 0.15	V _{REF} + 0.15	V _{CCIO} + 0.24	0.25 × V _{CCIO}	0.75 × V _{CCIO}	8	-8
HSTL-12 Class II	-0.15	V _{REF} - 0.08	V _{REF} + 0.08	V _{CCIO} + 0.15	-0.24	V _{REF} - 0.15	V _{REF} + 0.15	V _{CCIO} + 0.24	0.25 × V _{CCIO}	0.75 × V _{CCIO}	14	-14
HSUL-12	—	V _{REF} - 0.13	V _{REF} + 0.13	—	—	V _{REF} - 0.22	V _{REF} + 0.22	—	0.1 × V _{CCIO}	0.9 × V _{CCIO}	—	—

Differential SSTL I/O Standards Specifications

Differential SSTL requires a V_{REF} input.

Table 23. Differential SSTL I/O Standards Specifications for Intel MAX 10 Devices

I/O Standard	V _{CCIO} (V)			V _{Swing(DC)} (V)		V _{X(AC)} (V)			V _{Swing(AC)} (V)	
	Min	Typ	Max	Min	Max ⁽¹⁷⁾	Min	Typ	Max	Min	Max
SSTL-2 Class I, II	2.375	2.5	2.625	0.36	V _{CCIO}	V _{CCIO} /2 - 0.2	—	V _{CCIO} /2 + 0.2	0.7	V _{CCIO}
SSTL-18 Class I, II	1.7	1.8	1.9	0.25	V _{CCIO}	V _{CCIO} /2 - 0.175	—	V _{CCIO} /2 + 0.175	0.5	V _{CCIO}
SSTL-15 Class I, II	1.425	1.5	1.575	0.2	—	V _{CCIO} /2 - 0.15	—	V _{CCIO} /2 + 0.15	2(V _{IH(AC)} - V _{REF})	2(V _{IL(AC)} - V _{REF})
SSTL-135	1.283	1.35	1.45	0.18	—	V _{REF} - 0.135	0.5 × V _{CCIO}	V _{REF} + 0.135	2(V _{IH(AC)} - V _{REF})	2(V _{IL(AC)} - V _{REF})

Differential HSTL and HSUL I/O Standards Specifications

Differential HSTL requires a V_{REF} input.

⁽¹⁷⁾ The maximum value for V_{SWING(DC)} is not defined. However, each single-ended signal needs to be within the respective single-ended limits (V_{IH(DC)} and V_{IL(DC)}).



Core Performance Specifications

Clock Tree Specifications

Table 26. Clock Tree Specifications for Intel MAX 10 Devices

Device	Performance					Unit
	-I6	-A6, -C7	-I7	-A7	-C8	
10M02	450	416	416	382	402	MHz
10M04	450	416	416	382	402	MHz
10M08	450	416	416	382	402	MHz
10M16	450	416	416	382	402	MHz
10M25	450	416	416	382	402	MHz
10M40	450	416	416	382	402	MHz
10M50	450	416	416	382	402	MHz

PLL Specifications

Table 27. PLL Specifications for Intel MAX 10 Devices

V_{CCD_PLL} should always be connected to V_{CCINT} through decoupling capacitor and ferrite bead.

Symbol	Parameter	Condition	Min	Typ	Max	Unit
f_{IN} ⁽²⁸⁾	Input clock frequency	—	5	—	472.5	MHz
f_{INPFD}	Phase frequency detector (PFD) input frequency	—	5	—	325	MHz

continued...

⁽²⁸⁾ This parameter is limited in the Intel Quartus Prime software by the I/O maximum frequency. The maximum I/O frequency is different for each I/O standard.



Symbol	Parameter	Condition	Min	Typ	Max	Unit
t_{PLL_PSERR}	Accuracy of PLL phase shift	—	—	—	± 50	ps
t_{ARESET}	Minimum pulse width on areset signal.	—	10	—	—	ns
$t_{CONFIGPLL}$	Time required to reconfigure scan chains for PLLs	—	—	3.5 ⁽³²⁾	—	SCANCLK cycles
$f_{SCANCLK}$	scanclk frequency	—	—	—	100	MHz

Table 28. PLL Specifications for Intel MAX 10 Single Supply Devices

For V36 package, the PLL specification is based on single supply devices.

Symbol	Parameter	Condition	Max	Unit
$t_{OUTJITTER_PERIOD_DEDCLK}$ ⁽³¹⁾	Dedicated clock output period jitter	$F_{OUT} \geq 100$ MHz	660	ps
		$F_{OUT} < 100$ MHz	66	mUI
$t_{OUTJITTER_CCJ_DEDCLK}$ ⁽³¹⁾	Dedicated clock output cycle-to-cycle jitter	$F_{OUT} \geq 100$ MHz	660	ps
		$F_{OUT} < 100$ MHz	66	mUI

Table 29. PLL Specifications for Intel MAX 10 Dual Supply Devices

Symbol	Parameter	Condition	Max	Unit
$t_{OUTJITTER_PERIOD_DEDCLK}$ ⁽³¹⁾	Dedicated clock output period jitter	$F_{OUT} \geq 100$ MHz	300	ps
		$F_{OUT} < 100$ MHz	30	mUI
$t_{OUTJITTER_CCJ_DEDCLK}$ ⁽³¹⁾	Dedicated clock output cycle-to-cycle jitter	$F_{OUT} \geq 100$ MHz	300	ps
		$F_{OUT} < 100$ MHz	30	mUI

(32) With 100 MHz scanclk frequency.



Symbol	Parameter	Mode	-I6, -A6, -C7, -I7			-A7			-C8			Unit
			Min	Typ	Max	Min	Typ	Max	Min	Typ	Max	
		×4	40	—	300	40	—	300	40	—	300	Mbps
		×2	20	—	300	20	—	300	20	—	300	Mbps
		×1	10	—	300	10	—	300	10	—	300	Mbps
t _{DUTY}	Duty cycle on transmitter output clock	—	45	—	55	45	—	55	45	—	55	%
TCCS ⁽⁵⁷⁾	Transmitter channel-to-channel skew	—	—	—	300	—	—	300	—	—	300	ps
t _{x_Jitter} ⁽⁵⁸⁾	Output jitter (high-speed I/O performance pin)	—	—	—	425	—	—	425	—	—	425	ps
	Output jitter (low-speed I/O performance pin)	—	—	—	470	—	—	470	—	—	470	ps
t _{RISE}	Rise time	20 – 80%, C _{LOAD} = 5 pF	—	500	—	—	500	—	—	500	—	ps
t _{FALL}	Fall time	20 – 80%, C _{LOAD} = 5 pF	—	500	—	—	500	—	—	500	—	ps
t _{LOCK}	Time required for the PLL to lock, after CONF_DONE signal goes high, indicating the completion of device configuration	—	—	—	1	—	—	1	—	—	1	ms

(57) TCCS specifications apply to I/O banks from the same side only.

(58) TX jitter is the jitter induced from core noise and I/O switching noise.

Emulated RSDS_E_1R Transmitter Timing Specifications

Table 39. Emulated RSDS_E_1R Transmitter Timing Specifications for Intel MAX 10 Dual Supply Devices

Emulated RSDS_E_1R transmitter is supported at the output pin of all I/O banks.

Symbol	Parameter	Mode	-I6, -A6, -C7, -I7			-A7			-C8			Unit
			Min	Typ	Max	Min	Typ	Max	Min	Typ	Max	
f_{HSCLK}	Input clock frequency (high-speed I/O performance pin)	×10	5	—	85	5	—	85	5	—	85	MHz
		×8	5	—	85	5	—	85	5	—	85	MHz
		×7	5	—	85	5	—	85	5	—	85	MHz
		×4	5	—	85	5	—	85	5	—	85	MHz
		×2	5	—	85	5	—	85	5	—	85	MHz
		×1	5	—	170	5	—	170	5	—	170	MHz
HSIODR	Data rate (high-speed I/O performance pin)	×10	100	—	170	100	—	170	100	—	170	Mbps
		×8	80	—	170	80	—	170	80	—	170	Mbps
		×7	70	—	170	70	—	170	70	—	170	Mbps
		×4	40	—	170	40	—	170	40	—	170	Mbps
		×2	20	—	170	20	—	170	20	—	170	Mbps
		×1	10	—	170	10	—	170	10	—	170	Mbps
f_{HSCLK}	Input clock frequency (low-speed I/O performance pin)	×10	5	—	85	5	—	85	5	—	85	MHz
		×8	5	—	85	5	—	85	5	—	85	MHz
		×7	5	—	85	5	—	85	5	—	85	MHz
		×4	5	—	85	5	—	85	5	—	85	MHz
		×2	5	—	85	5	—	85	5	—	85	MHz
		×1	5	—	170	5	—	170	5	—	170	MHz
HSIODR	Data rate (low-speed I/O performance pin)	×10	100	—	170	100	—	170	100	—	170	Mbps
		×8	80	—	170	80	—	170	80	—	170	Mbps
		×7	70	—	170	70	—	170	70	—	170	Mbps

continued...

True Mini-LVDS and Emulated Mini-LVDS_E_3R Transmitter Timing Specifications

Table 40. True Mini-LVDS and Emulated Mini-LVDS_E_3R Transmitter Timing Specifications for Intel MAX 10 Dual Supply Devices

True **mini-LVDS** transmitter is only supported at the bottom I/O banks. Emulated **mini-LVDS_E_3R** transmitter is supported at the output pin of all I/O banks.

Symbol	Parameter	Mode	-I6, -A6, -C7, -I7			-A7			-C8			Unit
			Min	Typ	Max	Min	Typ	Max	Min	Typ	Max	
f_{HSCLK}	Input clock frequency (high-speed I/O performance pin)	×10	5	—	155	5	—	155	5	—	155	MHz
		×8	5	—	155	5	—	155	5	—	155	MHz
		×7	5	—	155	5	—	155	5	—	155	MHz
		×4	5	—	155	5	—	155	5	—	155	MHz
		×2	5	—	155	5	—	155	5	—	155	MHz
		×1	5	—	310	5	—	310	5	—	310	MHz
HSIODR	Data rate (high-speed I/O performance pin)	×10	100	—	310	100	—	310	100	—	310	Mbps
		×8	80	—	310	80	—	310	80	—	310	Mbps
		×7	70	—	310	70	—	310	70	—	310	Mbps
		×4	40	—	310	40	—	310	40	—	310	Mbps
		×2	20	—	310	20	—	310	20	—	310	Mbps
		×1	10	—	310	10	—	310	10	—	310	Mbps
f_{HSCLK}	Input clock frequency (low-speed I/O performance pin)	×10	5	—	150	5	—	150	5	—	150	MHz
		×8	5	—	150	5	—	150	5	—	150	MHz
		×7	5	—	150	5	—	150	5	—	150	MHz
		×4	5	—	150	5	—	150	5	—	150	MHz
		×2	5	—	150	5	—	150	5	—	150	MHz
		×1	5	—	300	5	—	300	5	—	300	MHz
HSIODR	Data rate (low-speed I/O performance pin)	×10	100	—	300	100	—	300	100	—	300	Mbps
		×8	80	—	300	80	—	300	80	—	300	Mbps

continued...



Symbol	Parameter	Mode	-I6, -A6, -C7, -I7			-A7			-C8			Unit
			Min	Typ	Max	Min	Typ	Max	Min	Typ	Max	
		×7	70	—	300	70	—	300	70	—	300	Mbps
		×4	40	—	300	40	—	300	40	—	300	Mbps
		×2	20	—	300	20	—	300	20	—	300	Mbps
		×1	10	—	300	10	—	300	10	—	300	Mbps
t _{DUTY}	Duty cycle on transmitter output clock	—	45	—	55	45	—	55	45	—	55	%
TCCS ⁽⁶¹⁾	Transmitter channel-to-channel skew	—	—	—	300	—	—	300	—	—	300	ps
t _{x_jitter} ⁽⁶²⁾	Output jitter (high-speed I/O performance pin)	—	—	—	425	—	—	425	—	—	425	ps
	Output jitter (low-speed I/O performance pin)	—	—	—	470	—	—	470	—	—	470	ps
t _{RISE}	Rise time	20 – 80%, C _{LOAD} = 5 pF	—	500	—	—	500	—	—	500	—	ps
t _{FALL}	Fall time	20 – 80%, C _{LOAD} = 5 pF	—	500	—	—	500	—	—	500	—	ps
t _{LOCK}	Time required for the PLL to lock, after CONF_DONE signal goes high, indicating the completion of device configuration	—	—	—	1	—	—	1	—	—	1	ms

(61) TCCS specifications apply to I/O banks from the same side only.

(62) TX jitter is the jitter induced from core noise and I/O switching noise.

True LVDS Transmitter Timing

Single Supply Devices True LVDS Transmitter Timing Specifications

Table 41. True LVDS Transmitter Timing Specifications for Intel MAX 10 Single Supply Devices

True **LVDS** transmitter is only supported at the bottom I/O banks.

Symbol	Parameter	Mode	-C7, -I7			-A7			-C8			Unit
			Min	Typ	Max	Min	Typ	Max	Min	Typ	Max	
f_{HSCLK}	Input clock frequency	×10	5	—	145	5	—	100	5	—	100	MHz
		×8	5	—	145	5	—	100	5	—	100	MHz
		×7	5	—	145	5	—	100	5	—	100	MHz
		×4	5	—	145	5	—	100	5	—	100	MHz
		×2	5	—	145	5	—	100	5	—	100	MHz
		×1	5	—	290	5	—	200	5	—	200	MHz
HSIODR	Data rate	×10	100	—	290	100	—	200	100	—	200	Mbps
		×8	80	—	290	80	—	200	80	—	200	Mbps
		×7	70	—	290	70	—	200	70	—	200	Mbps
		×4	40	—	290	40	—	200	40	—	200	Mbps
		×2	20	—	290	20	—	200	20	—	200	Mbps
		×1	10	—	290	10	—	200	10	—	200	Mbps
t_{DUTY}	Duty cycle on transmitter output clock	—	45	—	55	45	—	55	45	—	55	%
TCCS ⁽⁶³⁾	Transmitter channel-to-channel skew	—	—	—	300	—	—	300	—	—	300	ps
$t_{x\ Jitter}^{(64)}$	Output jitter	—	—	—	1,000	—	—	1,000	—	—	1,000	ps

continued...

(63) TCCS specifications apply to I/O banks from the same side only.

(64) TX jitter is the jitter induced from core noise and I/O switching noise.

Symbol	Parameter	Mode	-I6			-A6, -C7, -I7			-A7			-C8			Unit
			Min	Typ	Max	Min	Typ	Max	Min	Typ	Max	Min	Typ	Max	
		×1	10	—	360	10	—	350	10	—	320	10	—	320	Mbps
t _{DUTY}	Duty cycle on transmitter output clock	—	45	—	55	45	—	55	45	—	55	45	—	55	%
TCCS ⁽⁶⁵⁾	Transmitter channel-to-channel skew	—	—	—	300	—	—	300	—	—	300	—	—	300	ps
t _{x Jitter} ⁽⁶⁶⁾	Output jitter	—	—	—	380	—	—	380	—	—	380	—	—	380	ps
t _{RISE}	Rise time	20 – 80%, C _{LOAD} = 5 pF	—	500	—	—	500	—	—	500	—	—	500	—	ps
t _{FALL}	Fall time	20 – 80%, C _{LOAD} = 5 pF	—	500	—	—	500	—	—	500	—	—	500	—	ps
t _{LOCK}	Time required for the PLL to lock, after CONF_DONE signal goes high, indicating the completion of device configuration	—	—	—	1	—	—	1	—	—	1	—	—	1	ms

(65) TCCS specifications apply to I/O banks from the same side only.

(66) TX jitter is the jitter induced from core noise and I/O switching noise.



Emulated LVDS_E_3R, SLVS, and Sub-LVDS Transmitter Timing Specifications

Single Supply Devices Emulated LVDS_E_3R Transmitter Timing Specifications

Table 43. Emulated LVDS_E_3R Transmitter Timing Specifications for Intel MAX 10 Single Supply Devices

Emulated **LVDS_E_3R** transmitters are supported at the output pin of all I/O banks.

Symbol	Parameter	Mode	-C7, -I7			-A7			-C8			Unit
			Min	Typ	Max	Min	Typ	Max	Min	Typ	Max	
f_{HSCLK}	Input clock frequency (high-speed I/O performance pin)	×10	5	—	142.5	5	—	100	5	—	100	MHz
		×8	5	—	142.5	5	—	100	5	—	100	MHz
		×7	5	—	142.5	5	—	100	5	—	100	MHz
		×4	5	—	142.5	5	—	100	5	—	100	MHz
		×2	5	—	142.5	5	—	100	5	—	100	MHz
		×1	5	—	285	5	—	200	5	—	200	MHz
HSIODR	Data rate (high-speed I/O performance pin)	×10	100	—	285	100	—	200	100	—	200	Mbps
		×8	80	—	285	80	—	200	80	—	200	Mbps
		×7	70	—	285	70	—	200	70	—	200	Mbps
		×4	40	—	285	40	—	200	40	—	200	Mbps
		×2	20	—	285	20	—	200	20	—	200	Mbps
		×1	10	—	285	10	—	200	10	—	200	Mbps
f_{HSCLK}	Input clock frequency (low-speed I/O performance pin)	×10	5	—	100	5	—	100	5	—	100	MHz
		×8	5	—	100	5	—	100	5	—	100	MHz
		×7	5	—	100	5	—	100	5	—	100	MHz
		×4	5	—	100	5	—	100	5	—	100	MHz
		×2	5	—	100	5	—	100	5	—	100	MHz
		×1	5	—	200	5	—	200	5	—	200	MHz
HSIODR	Data rate (low-speed I/O performance pin)	×10	100	—	200	100	—	200	100	—	200	Mbps

continued...



Symbol	Parameter	Mode	-I6, -A6, -C7, -I7		-A7		-C8		Unit
			Min	Max	Min	Max	Min	Max	
	Sampling window (low-speed I/O performance pin)	—	—	910	—	910	—	910	ps
t_x Jitter ⁽⁷²⁾	Input jitter	—	—	500	—	500	—	500	ps
t_{LOCK}	Time required for the PLL to lock, after CONF_DONE signal goes high, indicating the completion of device configuration	—	—	1	—	1	—	1	ms

Memory Standards Supported by the Soft Memory Controller

Table 47. Memory Standards Supported by the Soft Memory Controller for Intel MAX 10 Devices

Contact your local sales representatives for access to the -I6 or -A6 speed grade devices in the Intel Quartus Prime software.

External Memory Interface Standard	Rate Support	Speed Grade	Voltage (V)	Max Frequency (MHz)
DDR3 SDRAM	Half	-I6	1.5	303
DDR3L SDRAM	Half	-I6	1.35	303
DDR2 SDRAM	Half	-I6	1.8	200
		-I7 and -C7		167
LPDDR2 ⁽⁷³⁾	Half	-I6	1.2	200 ⁽⁷⁴⁾

Related Information

External Memory Interface Spec Estimator

Provides the specific details of the memory standards supported.

(72) TX jitter is the jitter induced from core noise and I/O switching noise.

(73) Intel MAX 10 devices support only single-die LPDDR2.

(74) To achieve the specified performance, constrain the memory device I/O and core power supply variation to within $\pm 3\%$. By default, the frequency is 167 MHz.



Device	CFM Data Size (bits)	
	Without Memory Initialization	With Memory Initialization
10M25	4,140,000	4,780,000
10M40	7,840,000	9,670,000
10M50	7,840,000	9,670,000

Internal Configuration Time

The internal configuration time measurement is from the rising edge of nSTATUS signal to the rising edge of CONF_DONE signal.

Table 53. Internal Configuration Time for Intel MAX 10 Devices (Uncompressed .rbf)

Device	Internal Configuration Time (ms)							
	Unencrypted				Encrypted			
	Without Memory Initialization		With Memory Initialization		Without Memory Initialization		With Memory Initialization	
	Min	Max	Min	Max	Min	Max	Min	Max
10M02	0.3	1.7	—	—	1.7	5.4	—	—
10M04	0.6	2.7	1.0	3.4	5.0	15.0	6.8	19.6
10M08	0.6	2.7	1.0	3.4	5.0	15.0	6.8	19.6
10M16	1.1	3.7	1.4	4.5	9.3	25.3	11.7	31.5
10M25	1.0	3.7	1.3	4.4	14.0	38.1	16.9	45.7
10M40	2.6	6.9	3.2	9.8	41.5	112.1	51.7	139.6
10M50	2.6	6.9	3.2	9.8	41.5	112.1	51.7	139.6



Programmable IOE Delay for Column Pins

Table 58. IOE Programmable Delay on Column Pins for Intel MAX 10 Devices

The incremental values for the settings are generally linear. For exact values of each setting, refer to the **Assignment Name** column in the latest version of the Intel Quartus Prime software.

The minimum and maximum offset timing numbers are in reference to setting '0' as available in the Intel Quartus Prime software.

Parameter	Paths Affected	Number of Settings	Minimum Offset	Maximum Offset							Unit	
				Fast Corner		Slow Corner						
				-I7	-C8	-A6	-C7	-C8	-I7	-A7		
Input delay from pin to internal cells	Pad to I/O dataout to core	7	0	0.81	0.868	1.823	1.802	1.864	1.862	1.912	ns	
Input delay from pin to input register	Pad to I/O input register	8	0	0.914	0.981	2.06	2.032	2.101	2.102	2.161	ns	
Delay from output register to output pin	I/O output register to pad	2	0	0.435	0.466	0.971	0.97	1.013	1.001	1.028	ns	



Date	Version	Changes
December 2017	2017.12.15	<ul style="list-style-type: none"> Removed the units for "Input resistance" and "Input capacitance" parameters in the following tables: <ul style="list-style-type: none"> — ADC Performance Specifications for Intel MAX 10 Single Supply Devices — ADC Performance Specifications for Intel MAX 10 Dual Supply Devices Removed the specification with memory initialization for 10M02 device in the Uncompressed .rbf Sizes for Intel MAX 10 Devices table.
June 2017	2017.06.16	<ul style="list-style-type: none"> Added notes for T_J for Industrial and Automotive devices in Recommended Operating Conditions for Intel MAX 10 Devices table. Updated the parameter in Internal Weak Pull-Up Resistor for Intel MAX 10 Devices table. Changed "Performance" to "Frequency" in UFM Performance Specifications for Intel MAX 10 Devices table. Removed PowerPlay text from tool name.
February 2017	2017.02.21	<ul style="list-style-type: none"> Rebranded as Intel.
October 2016	2016.10.31	<ul style="list-style-type: none"> Updated the note to the Intel MAX 10 Device Grades and Speed Grades Supported table. Updated the Memory Standards Supported by the Soft Memory Controller for Intel MAX 10 Devices table.
May 2016	2016.05.02	<ul style="list-style-type: none"> Updated t_{RAMP} Specifications in Recommended Operating Conditions for Intel MAX 10 Devices table. <ul style="list-style-type: none"> — Removed standard POR and fast POR specifications. — Updated maximum value from 3 ms to 10 ms and added a note for the minimum value. Added Supply Current and Power Consumption section. Added the following tables: <ul style="list-style-type: none"> — Memory Standards Supported by the Soft Memory Controller for Intel MAX 10 Devices — Internal Configuration Timing Parameter for Intel MAX 10 Devices Removed POR Delay Specifications for Intel MAX 10 Devices table. Updated the description in the Internal Configuration Time section. Updated the following tables: <ul style="list-style-type: none"> — Internal Configuration Time for Intel MAX 10 Devices (Uncompressed .rbf) — Internal Configuration Time for Intel MAX 10 Devices (Compressed .rbf)

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